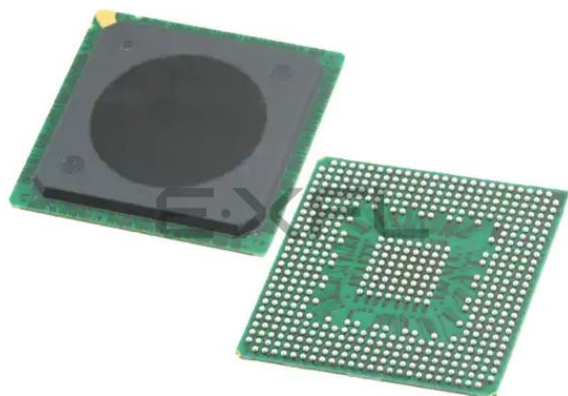




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Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e300c2
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	333MHz
Co-Processors/DSP	Communications; QUICC Engine
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100Mbps (3)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	516-BBGA
Supplier Device Package	516-PBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8321zqafdc

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8323E. The MPC8323E is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

Table 1 provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings¹

Characteristic		Symbol	Max Value	Unit	Notes
Core supply voltage		V_{DD}	–0.3 to 1.26	V	—
PLL supply voltage		AV_{DDn}	–0.3 to 1.26	V	—
DDR1 and DDR2 DRAM I/O voltage		GV_{DD}	–0.3 to 2.75 –0.3 to 1.98	V	—
PCI, local bus, DUART, system control and power management, I ² C, SPI, MII, RMII, MII management, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.6	V	—
Input voltage	DDR1/DDR2 DRAM signals	MV_{IN}	–0.3 to ($GV_{DD} + 0.3$)	V	2
	DDR1/DDR2 DRAM reference	MV_{REF}	–0.3 to ($GV_{DD} + 0.3$)	V	2
	Local bus, DUART, CLKIN, system control and power management, I ² C, SPI, and JTAG signals	OV_{IN}	–0.3 to ($OV_{DD} + 0.3$)	V	3
	PCI	OV_{IN}	–0.3 to ($OV_{DD} + 0.3$)	V	5
Storage temperature range		T_{STG}	–55 to 150	°C	—

Notes:

- Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
- Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.
- Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.

2.1.3 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	42	$OV_{DD} = 3.3 \text{ V}$
PCI signals	25	
DDR1 signal	18	$GV_{DD} = 2.5 \text{ V}$
DDR2 signal	18	$GV_{DD} = 1.8 \text{ V}$
DUART, system control, I2C, SPI, JTAG	42	$OV_{DD} = 3.3 \text{ V}$
GPIO signals	42	$OV_{DD} = 3.3 \text{ V}$

2.1.4 Input Capacitance Specification

Table 4 describes the input capacitance for the CLKIN pin in the MPC8323E.

Table 4. Input Capacitance Specification

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input capacitance for all pins except CLKIN	C_I	6	8	pF	—
Input capacitance for CLKIN	$C_{I\text{CLKIN}}$	10	—	pF	1

Note:

1. The external clock generator should be able to drive 10 pF.

2.2 Power Sequencing

The device does not require the core supply voltage (V_{DD}) and IO supply voltages (GV_{DD} and OV_{DD}) to be applied in any particular order. Note that during power ramp-up, before the power supplies are stable and if the I/O voltages are supplied before the core voltage, there might be a period of time that all input and output pins are actively driven and cause contention and excessive current. In order to avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltage (V_{DD}) before the I/O voltage (GV_{DD} and OV_{DD}) and assert $\overline{\text{PORESET}}$ before the power supplies fully ramp up. In the case where the core voltage is applied first, the core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V; see Figure 3. Once both the power supplies (I/O voltage and core voltage) are stable, wait for a minimum of 32 clock cycles before negating $\overline{\text{PORESET}}$.

Note that there is no specific power down sequence requirement for the device. I/O voltage supplies (GV_{DD} and OV_{DD}) do not have any ordering requirements with respect to one another.

Table 9. RESET Initialization Timing Specifications (continued)

Parameter/Condition	Min	Max	Unit	Notes
$\overline{\text{HRESET}}/\overline{\text{SRESET}}$ assertion (output)	512	—	$t_{\text{PCI_SYNC_IN}}$	1
$\overline{\text{HRESET}}$ negation to $\overline{\text{SRESET}}$ negation (output)	16	—	$t_{\text{PCI_SYNC_IN}}$	1
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of $\overline{\text{PORESET}}$ when the MPC8323E is in PCI host mode	4	—	t_{CLKIN}	2
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of $\overline{\text{PORESET}}$ when the MPC8323E is in PCI agent mode	4	—	$t_{\text{PCI_SYNC_IN}}$	1
Input hold time for POR config signals with respect to negation of $\overline{\text{HRESET}}$	0	—	ns	—
Time for the MPC8323E to turn off POR configuration signals with respect to the assertion of $\overline{\text{HRESET}}$	—	4	ns	3
Time for the MPC8323E to turn on POR configuration signals with respect to the negation of $\overline{\text{HRESET}}$	1	—	$t_{\text{PCI_SYNC_IN}}$	1, 3

Notes:

1. $t_{\text{PCI_SYNC_IN}}$ is the clock period of the input clock applied to PCI_SYNC_IN. When the MPC8323E is in PCI host mode the primary clock is applied to the CLKIN input, and PCI_SYNC_IN period depends on the value of CFG_CLKIN_DIV. See the *MPC8323E PowerQUICC II Pro Integrated Communications Processor Reference Manual* for more details.
2. t_{CLKIN} is the clock period of the input clock applied to CLKIN. It is only valid when the MPC8323E is in PCI host mode. See the *MPC8323E PowerQUICC II Pro Integrated Communications Processor Reference Manual* for more details.
3. POR configuration signals consists of CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV.

Table 10 provides the PLL lock times.

Table 10. PLL Lock Times

Parameter/Condition	Min	Max	Unit	Notes
PLL lock times	—	100	μs	—

5.1 Reset Signals DC Electrical Characteristics

Table 11 provides the DC electrical characteristics for the MPC8323E reset signals mentioned in Table 9.

Table 11. Reset Signals DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit	Notes
Output high voltage	V_{OH}	$I_{\text{OH}} = -6.0 \text{ mA}$	2.4	—	V	1
Output low voltage	V_{OL}	$I_{\text{OL}} = 6.0 \text{ mA}$	—	0.5	V	1
Output low voltage	V_{OL}	$I_{\text{OL}} = 3.2 \text{ mA}$	—	0.4	V	1
Input high voltage	V_{IH}	—	2.0	$\text{OV}_{\text{DD}} + 0.3$	V	1
Input low voltage	V_{IL}	—	-0.3	0.8	V	—

Table 13. DDR2 SDRAM Capacitance for $Dn_GV_{DD}(typ) = 1.8\text{ V}$

Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1
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Note:

1. This parameter is sampled. $Dn_GV_{DD} = 1.8\text{ V} \pm 0.090\text{ V}$, $f = 1\text{ MHz}$, $T_A = 25\text{ }^\circ\text{C}$, $V_{OUT} = Dn_GV_{DD} \div 2$, V_{OUT} (peak-to-peak) = 0.2 V.

Table 14 provides the recommended operating conditions for the DDR1 SDRAM component(s) of the MPC8323E when $Dn_GV_{DD}(typ) = 2.5\text{ V}$.

Table 14. DDR1 SDRAM DC Electrical Characteristics for $Dn_GV_{DD}(typ) = 2.5\text{ V}$

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	Dn_GV_{DD}	2.375	2.625	V	1
I/O reference voltage	$MVREF_{REF}$	$0.49 \times Dn_GV_{DD}$	$0.51 \times Dn_GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MVREF_{REF} - 0.04$	$MVREF_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MVREF_{REF} + 0.15$	$Dn_GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	-0.3	$MVREF_{REF} - 0.15$	V	—
Output leakage current	I_{OZ}	-9.9	-9.9	μA	4
Output high current ($V_{OUT} = 1.95\text{ V}$)	I_{OH}	-16.2	—	mA	—
Output low current ($V_{OUT} = 0.35\text{ V}$)	I_{OL}	16.2	—	mA	—

Notes:

1. Dn_GV_{DD} is expected to be within 50 mV of the DRAM Dn_GV_{DD} at all times.
2. $MVREF_{REF}$ is expected to be equal to $0.5 \times Dn_GV_{DD}$, and to track Dn_GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on $MVREF_{REF}$ may not exceed $\pm 2\%$ of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to $MVREF_{REF}$. This rail should track variations in the DC level of $MVREF_{REF}$.
4. Output leakage is measured with all outputs disabled, $0\text{ V} \leq V_{OUT} \leq Dn_GV_{DD}$.

Table 15 provides the DDR1 capacitance $Dn_GV_{DD}(typ) = 2.5\text{ V}$.

Table 15. DDR1 SDRAM Capacitance for $Dn_GV_{DD}(typ) = 2.5\text{ V}$ Interface

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. $Dn_GV_{DD} = 2.5\text{ V} \pm 0.125\text{ V}$, $f = 1\text{ MHz}$, $T_A = 25\text{ }^\circ\text{C}$, $V_{OUT} = Dn_GV_{DD} \div 2$, V_{OUT} (peak-to-peak) = 0.2 V.

Table 24. MII Receive AC Timing Specifications (continued)

At recommended operating conditions with OV_{DD} of $3.3\text{ V} \pm 10\%$.

Parameter/Condition	Symbol ¹	Min	Typical	Max	Unit
RX_CLK clock fall time	t_{MRXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 8 provides the AC test load.

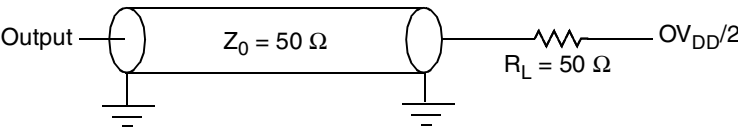


Figure 8. AC Test Load

Figure 9 shows the MII receive AC timing diagram.

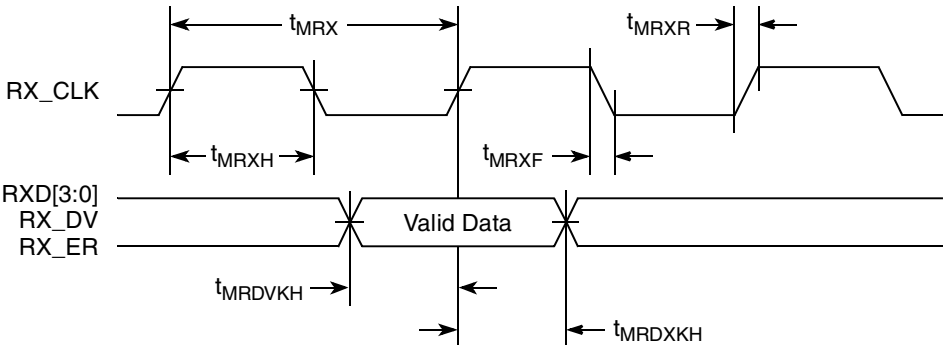


Figure 9. MII Receive AC Timing Diagram

8.2.2 RMII AC Timing Specifications

This section describes the RMII transmit and receive AC timing specifications.

Table 26. RMII Receive AC Timing Specifications (continued)

At recommended operating conditions with OV_{DD} of $3.3\text{ V} \pm 10\%$.

Parameter/Condition	Symbol ¹	Min	Typical	Max	Unit
REF_CLK clock fall time $V_{IH}(\text{max})$ to $V_{IL}(\text{min})$	t_{RMXF}	1.0	—	4.0	ns

Note:

- The symbols used for timing specifications follow the pattern of $t_{(\text{first three letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, $t_{RMRDVKH}$ symbolizes RMII receive timing (RMR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{RMX} clock reference (K) going to the high (H) state or setup time. Also, $t_{RMRDXKL}$ symbolizes RMII receive timing (RMR) with respect to the time data input signals (D) went invalid (X) relative to the t_{RMX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{RMX} represents the RMII (RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 11 provides the AC test load.

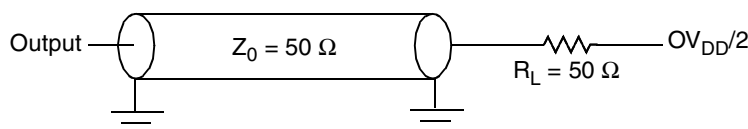
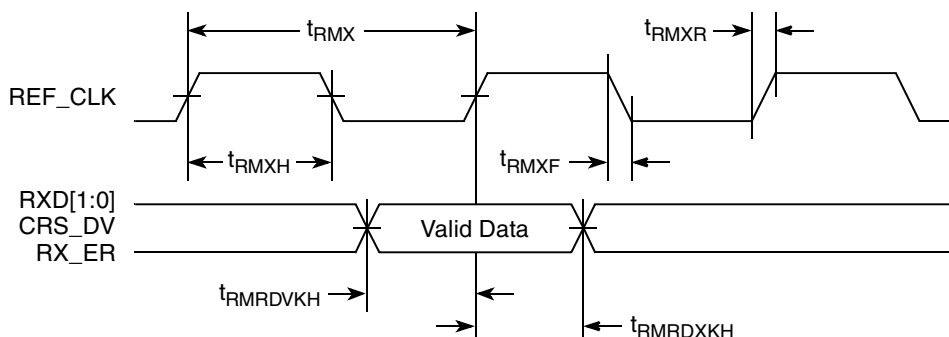

Figure 11. AC Test Load

Figure 12 shows the RMII receive AC timing diagram.


Figure 12. RMII Receive AC Timing Diagram

8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for MII, and RMII are specified in [Section 8.1, “Ethernet Controller \(10/100 Mbps\)—MII/RMII Electrical Characteristics.”](#)

8.3.1 MII Management DC Electrical Characteristics

MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in [Table 27](#).

Table 27. MII Management DC Electrical Characteristics When Powered at 3.3 V

Parameter	Symbol	Conditions	Min	Max	Unit
Supply voltage (3.3 V)	OV_{DD}	—	2.97	3.63	V
Output high voltage	V_{OH}	$I_{OH} = -1.0 \text{ mA}$ $OV_{DD} = \text{Min}$	2.10	$OV_{DD} + 0.3$	V
Output low voltage	V_{OL}	$I_{OL} = 1.0 \text{ mA}$ $OV_{DD} = \text{Min}$	GND	0.50	V
Input high voltage	V_{IH}	—	2.00	—	V
Input low voltage	V_{IL}	—	—	0.80	V
Input current	I_{IN}	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$	—	± 5	μA

8.3.2 MII Management AC Electrical Specifications

[Table 28](#) provides the MII management AC timing specifications.

Table 28. MII Management AC Timing Specifications

At recommended operating conditions with OV_{DD} is 3.3 V $\pm 10\%$.

Parameter/Condition	Symbol ¹	Min	Typical	Max	Unit	Notes
MDC frequency	f_{MDC}	—	2.5	—	MHz	—
MDC period	t_{MDC}	—	400	—	ns	—
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	—
MDC to MDIO delay	t_{MDKHDX}	10	—	70	ns	—
MDIO to MDC setup time	t_{MDDVKH}	5	—	—	ns	—
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	—
MDC rise time	t_{MDCR}	—	—	10	ns	—
MDC fall time	t_{MDHF}	—	—	10	ns	—

Note:

- The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 13 shows the MII management AC timing diagram.

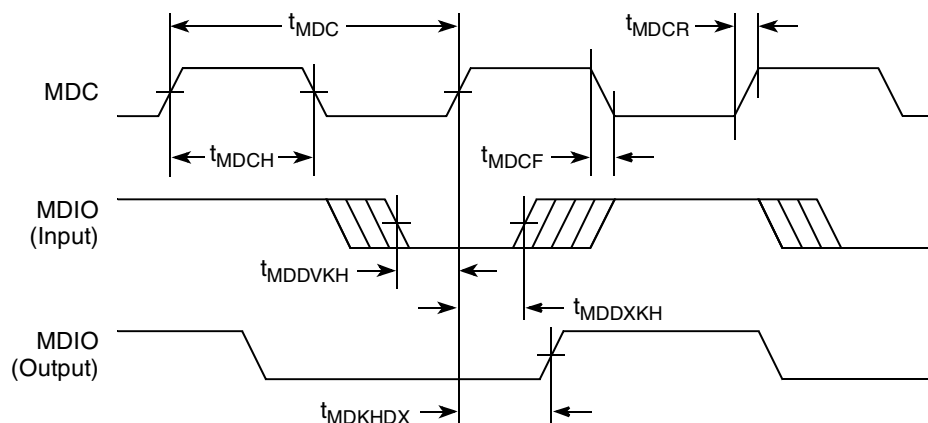


Figure 13. MII Management Interface Timing Diagram

9 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8323E.

9.1 Local Bus DC Electrical Characteristics

Table 29 provides the DC electrical characteristics for the local bus interface.

Table 29. Local Bus DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	$OV_{DD} + 0.3$	V
Low-level input voltage	V_{IL}	-0.3	0.8	V
High-level output voltage, $I_{OH} = -100 \mu A$	V_{OH}	$OV_{DD} - 0.2$	—	V
Low-level output voltage, $I_{OL} = 100 \mu A$	V_{OL}	—	0.2	V
Input current	I_{IN}	—	± 5	μA

9.2 Local Bus AC Electrical Specifications

Table 30 describes the general timing parameters of the local bus interface of the MPC8323E.

Table 30. Local Bus General Timing Parameters

Parameter	Symbol ¹	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	15	—	ns	2
Input setup to local bus clock (LCLK _n)	t_{LBIVKH}	7	—	ns	3, 4
Input hold from local bus clock (LCLK _n)	t_{LBIXKH}	1.0	—	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT1}$	1.5	—	ns	5

Table 32. JTAG AC Timing Specifications (Independent of CLKIN)¹ (continued)

At recommended operating conditions (see Table 2).

Parameter	Symbol ²	Min	Max	Unit	Notes
JTAG external clock to output high impedance:				ns	
Boundary-scan data	t_{JTKLDZ}	2	19		5, 6
TDO	t_{JTKLOZ}	2	9		6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50- Ω load (see Figure 14). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{JTDVXH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDVXH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{TRST}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK} .
5. Non-JTAG signal output timing with respect to t_{TCLK} .
6. Guaranteed by design and characterization.

Figure 18 provides the AC test load for TDO and the boundary-scan outputs of the MPC8323E.

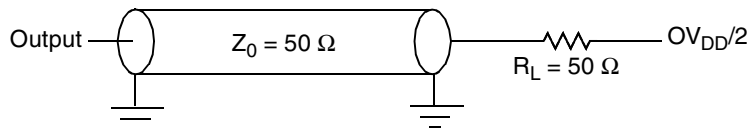

Figure 18. AC Test Load for the JTAG Interface

Figure 19 provides the JTAG clock input timing diagram.

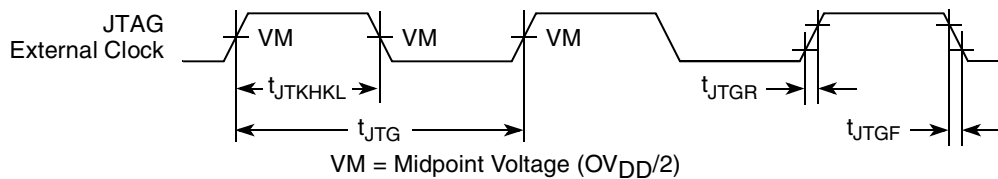

Figure 19. JTAG Clock Input Timing Diagram

Figure 20 provides the $\overline{TRST}$ timing diagram.

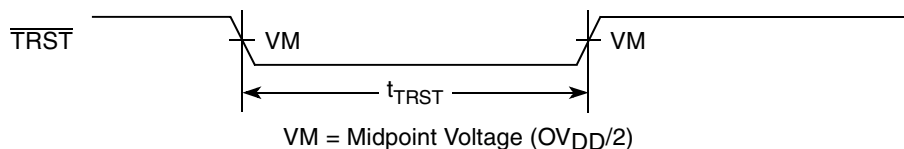

Figure 20. $\overline{TRST}$ Timing Diagram

Table 34. I²C AC Electrical Specifications (continued)

All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 33).

Parameter	Symbol ¹	Min	Max	Unit
Rise time of both SDA and SCL signals	t_{I2CR}	$20 + 0.1 C_b^4$	300	ns
Fall time of both SDA and SCL signals	t_{I2CF}	$20 + 0.1 C_b^4$	300	ns
Setup time for STOP condition	t_{I2PVKH}	0.6	—	μs
Bus free time between a STOP and START condition	t_{I2KHDX}	1.3	—	μs
Noise margin at the LOW level for each connected device (including hysteresis)	V_{NL}	$0.1 \times OV_{DD}$	—	V
Noise margin at the HIGH level for each connected device (including hysteresis)	V_{NH}	$0.2 \times OV_{DD}$	—	V

Notes:

- The symbols used for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{I2DVKH} symbolizes I²C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. Also, t_{I2SXKL} symbolizes I²C timing (I2) for the time that the data with respect to the start condition (S) went invalid (X) relative to the t_{I2C} clock reference (K) going to the low (L) state or hold time. Also, t_{I2PVKH} symbolizes I²C timing (I2) for the time that the data with respect to the stop condition (P) reaching the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
- MPC8323E provides a hold time of at least 300 ns for the SDA signal (referred to the V_{IH} (min) of the SCL signal) to bridge the undefined region of the falling edge of SCL.
- The maximum t_{I2DVKH} has only to be met if the device does not stretch the LOW period (t_{I2CL}) of the SCL signal.
- C_b = capacitance of one bus line in pF.

Figure 23 provides the AC test load for the I²C.

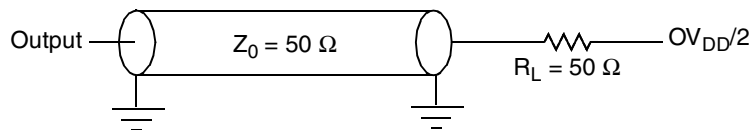
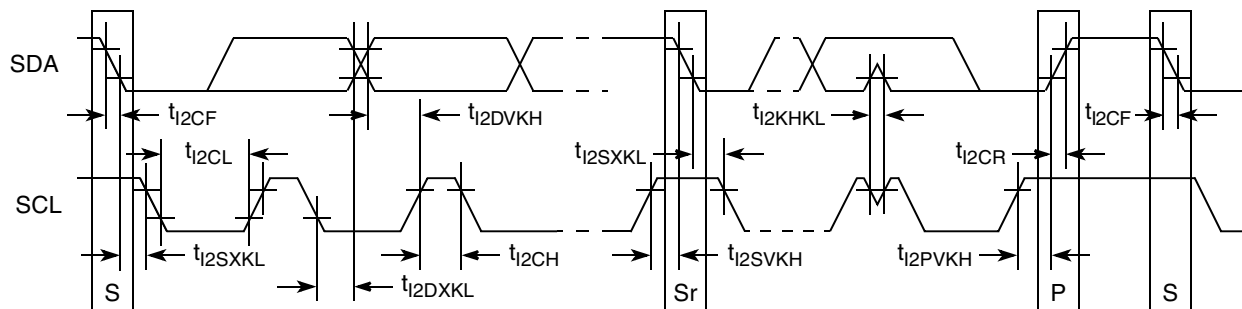

Figure 23. I²C AC Test Load

Figure 24 shows the AC timing diagram for the I²C bus.


Figure 24. I²C Bus AC Timing Diagram

12 PCI

This section describes the DC and AC electrical specifications for the PCI bus of the MPC8323E.

12.1 PCI DC Electrical Characteristics

Table 35 provides the DC electrical characteristics for the PCI interface of the MPC8323E.

Table 35. PCI DC Electrical Characteristics^{1,2}

Parameter	Symbol	Test Condition	Min	Max	Unit
High-level input voltage	V_{IH}	$V_{OUT} \geq V_{OH} \text{ (min) or}$	2	$OV_{DD} + 0.3$	V
Low-level input voltage	V_{IL}	$V_{OUT} \leq V_{OL} \text{ (max)}$	-0.3	0.8	V
High-level output voltage	V_{OH}	$OV_{DD} = \text{min},$ $I_{OH} = -100 \mu\text{A}$	$OV_{DD} - 0.2$	—	V
Low-level output voltage	V_{OL}	$OV_{DD} = \text{min},$ $I_{OL} = 100 \mu\text{A}$	—	0.2	V
Input current	I_{IN}	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$	—	± 5	μA

Notes:

- Note that the symbol V_{IN} , in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.
- Ranges listed do not meet the full range of the DC specifications of the *PCI 2.3 Local Bus Specifications*.

12.2 PCI AC Electrical Specifications

This section describes the general AC timing parameters of the PCI bus of the MPC8323E. Note that the PCI_CLK or PCI_SYNC_IN signal is used as the PCI input clock depending on whether the MPC8323E is configured as a host or agent device. Table 36 shows the PCI AC timing specifications at 66 MHz.

Table 36. PCI AC Timing Specifications at 66 MHz

Parameter	Symbol ¹	Min	Max	Unit	Notes
Clock to output valid	t_{PCKHOV}	—	6.0	ns	2
Output hold from clock	t_{PCKHOX}	1	—	ns	2
Clock to output high impedance	t_{PCKHOZ}	—	14	ns	2, 3
Input setup to clock	t_{PCIVKH}	3.0	—	ns	2, 4
Input hold from clock	t_{PCIXKH}	0	—	ns	2, 4

Notes:

- The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS} , reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
- See the timing measurement conditions in the *PCI 2.3 Local Bus Specifications*.
- For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
- Input timings are measured at the pin.

16 SPI

This section describes the DC and AC electrical specifications for the SPI of the MPC8323E.

16.1 SPI DC Electrical Characteristics

Table 44 provides the DC electrical characteristics for the MPC8323E SPI.

Table 44. SPI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	$I_{OH} = -6.0 \text{ mA}$	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 6.0 \text{ mA}$	—	0.5	V
Output low voltage	V_{OL}	$I_{OL} = 3.2 \text{ mA}$	—	0.4	V
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	-0.3	0.8	V
Input current	I_{IN}	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$	—	± 5	μA

16.2 SPI AC Timing Specifications

Table 45 and provide the SPI input and output AC timing specifications.

Table 45. SPI AC Timing Specifications¹

Characteristic	Symbol ²	Min	Max	Unit
SPI outputs—Master mode (internal clock) delay	$t_{NIKH OV}$	0.5	6	ns
SPI outputs—Slave mode (external clock) delay	$t_{NEKH OV}$	2	8	ns
SPI inputs—Master mode (internal clock) input setup time	t_{NIIVKH}	6	—	ns
SPI inputs—Master mode (internal clock) input hold time	t_{NIIXKH}	0	—	ns
SPI inputs—Slave mode (external clock) input setup time	t_{NEIVKH}	4	—	ns
SPI inputs—Slave mode (external clock) input hold time	t_{NEIXKH}	2	—	ns

Notes:

- Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
- The symbols used for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, $t_{NIKH OV}$ symbolizes the NMSI outputs internal timing (NI) for the time t_{SPI} memory clock reference (K) goes from the high state (H) until outputs (O) are valid (V).

Figure 30 provides the AC test load for the SPI.

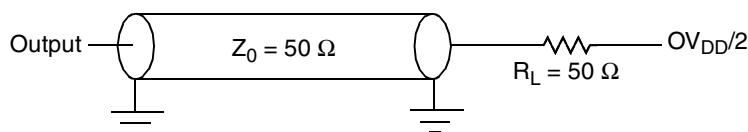


Figure 30. SPI AC Test Load

Figure 39 shows the timing with external clock.

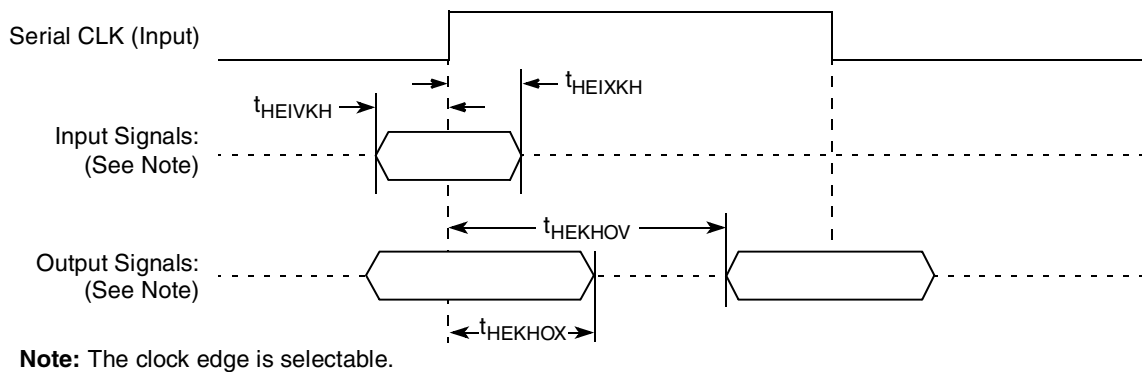


Figure 39. AC Timing (External Clock) Diagram

Figure 40 shows the timing with internal clock.

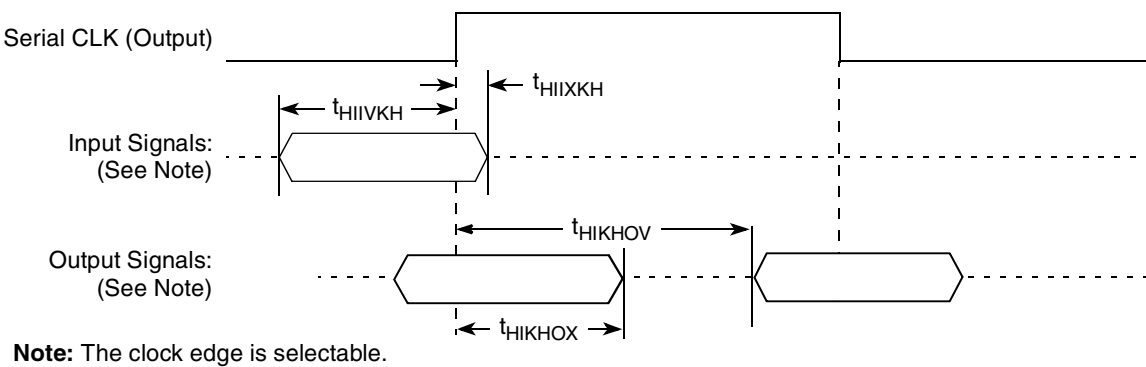
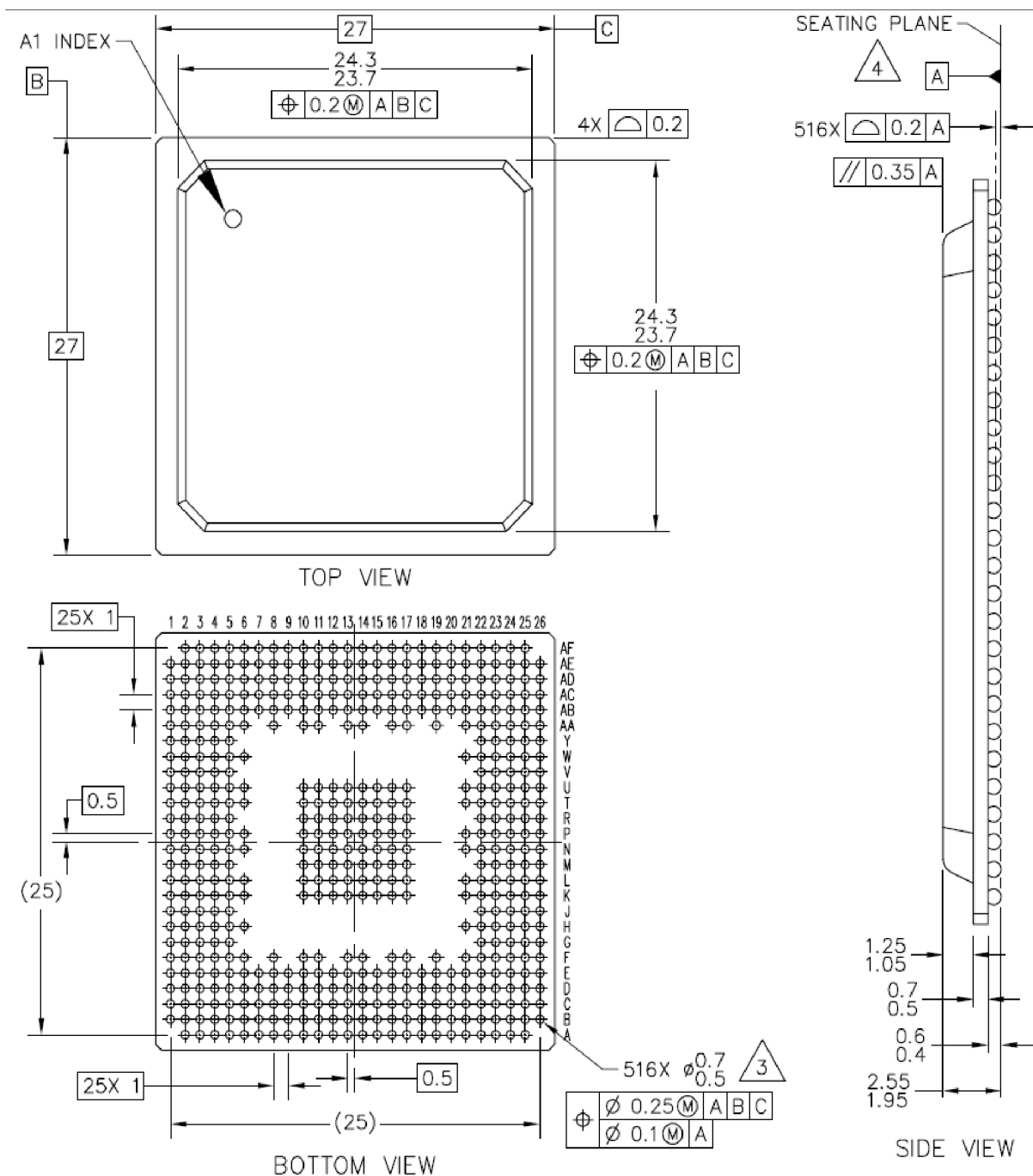


Figure 40. AC Timing (Internal Clock) Diagram



Notes:

1. All dimensions are in millimeters.
2. Dimensions and tolerances per ASME Y14.5M-1994.
3. Maximum solder ball diameter measured parallel to datum A.
4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.

Figure 42. Mechanical Dimensions and Bottom Surface Nomenclature of the MPC8323E PBGA

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MEMC_MCKE	AD14	O	GV _{DD}	3
MEMC_MCK	AF14	O	GV _{DD}	—
MEMC_MCK	AE14	O	GV _{DD}	—
MEMC_MODT	AF11	O	GV _{DD}	—
Local Bus Controller Interface				
LAD0	N25	IO	OV _{DD}	7
LAD1	P26	IO	OV _{DD}	7
LAD2	P25	IO	OV _{DD}	7
LAD3	R26	IO	OV _{DD}	7
LAD4	R25	IO	OV _{DD}	7
LAD5	T26	IO	OV _{DD}	7
LAD6	T25	IO	OV _{DD}	7
LAD7	U25	IO	OV _{DD}	7
LAD8	M24	IO	OV _{DD}	7
LAD9	N24	IO	OV _{DD}	7
LAD10	P24	IO	OV _{DD}	7
LAD11	R24	IO	OV _{DD}	7
LAD12	T24	IO	OV _{DD}	7
LAD13	U24	IO	OV _{DD}	7
LAD14	U26	IO	OV _{DD}	7
LAD15	V26	IO	OV _{DD}	7
LA16	K25	O	OV _{DD}	7
LA17	L25	O	OV _{DD}	7
LA18	L26	O	OV _{DD}	7
LA19	L24	O	OV _{DD}	7
LA20	M26	O	OV _{DD}	7
LA21	M25	O	OV _{DD}	7
LA22	N26	O	OV _{DD}	7
LA23	AC24	O	OV _{DD}	7
LA24	AC25	O	OV _{DD}	7
LA25	AB23	O	OV _{DD}	7
LCS0	AB24	O	OV _{DD}	4

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI_AD20	AB2	IO	OV _{DD}	—
PCI_AD21	Y4	IO	OV _{DD}	—
PCI_AD22	AC1	IO	OV _{DD}	—
PCI_AD23	AA3	IO	OV _{DD}	—
PCI_AD24	AA4	IO	OV _{DD}	—
PCI_AD25	AD1	IO	OV _{DD}	—
PCI_AD26	AD2	IO	OV _{DD}	—
PCI_AD27	AB3	IO	OV _{DD}	—
PCI_AD28	AB4	IO	OV _{DD}	—
PCI_AD29	AE1	IO	OV _{DD}	—
PCI_AD30	AC3	IO	OV _{DD}	—
PCI_AD31	AC4	IO	OV _{DD}	—
PCI_C_BE0	M4	IO	OV _{DD}	—
PCI_C_BE1	T4	IO	OV _{DD}	—
PCI_C_BE2	Y3	IO	OV _{DD}	—
PCI_C_BE3	AC2	IO	OV _{DD}	—
PCI_PAR	U3	IO	OV _{DD}	—
PCI_FRAME	W1	IO	OV _{DD}	5
PCI_TRDY	W4	IO	OV _{DD}	5
PCI_IRDY	W2	IO	OV _{DD}	5
PCI_STOP	V4	IO	OV _{DD}	5
PCI_DEVSEL	W3	IO	OV _{DD}	5
PCI_IDSEL	P2	I	OV _{DD}	—
PCI_SERR	U4	IO	OV _{DD}	5
PCI_PERR	V3	IO	OV _{DD}	5
PCI_REQ0	AD4	IO	OV _{DD}	—
PCI_REQ1/CPCI_HS_ES	AE3	I	OV _{DD}	—
PCI_REQ2	AF3	I	OV _{DD}	—
PCI_GNT0	AD3	IO	OV _{DD}	—
PCI_GNT1/CPCI_HS_LED	AE4	O	OV _{DD}	—
PCI_GNT2/CPCI_HS_ENUM	AF4	O	OV _{DD}	—
M66EN	L4	I	OV _{DD}	—

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
V_{DD}	K10, K11, K12, K13, K14, K15, K16, K17, L10, L17, M10, M17, N10, N17, P10, P17, R10, R17, T10, T17, U10, U11, U12, U13, U14, U15, U16, U17	V_{DD}	—	—
V_{SS}	B23, E7, E11, E13, E17, E21, F11, F13, F17, F21, F23, G5, H22, K5, K6, L11, L12, L13, L14, L15, L16, L21, M11, M12, M13, M14, M15, M16, N6, N11, N12, N13, N14, N15, N16, P5, P11, P12, P13, P14, P15, P16, P21, R11, R12, R13, R14, R15, R16, R22, T6, T11, T12, T13, T14, T15, T16, U5, U21, V23, W5, W6, W21, W23, W24, Y22, AA5, AA6, AA22, AA25, AB7, AB13, AB19, AB22, AC10, AC12, AC16, AC20	V_{SS}	—	—
No Connect				
NC	C22	—	—	—

Notes:

1. This pin is an open drain signal. A weak pull-up resistor (1 k Ω) should be placed on this pin to OV_{DD} .
2. This pin is an open drain signal. A weak pull-up resistor (2–10 k Ω) should be placed on this pin to OV_{DD} .
3. This output is actively driven during reset rather than being three-stated during reset.
4. These JTAG and local bus pins have weak internal pull-up P-FETs that are always enabled.
5. This pin should have a weak pull up if the chip is in PCI host mode. Follow the PCI specification's recommendation.
6. This pin must always be tied to GND. 7. This pin has weak internal pull-down N-FET that is always enabled. 8. Though this pin has weak internal pull-up yet it is recommended to apply an external pull-up.

22.7 Suggested PLL Configurations

To simplify the PLL configurations, the MPC8323E might be separated into two clock domains. The first domain contain the CSB PLL and the core PLL. The core PLL is connected serially to the CSB PLL, and has the csb_clk as its input clock. The second clock domain has the QUICC Engine PLL. The clock domains are independent, and each of their PLLs are configured separately. Both of the domains has one common input clock. Table 63 shows suggested PLL configurations for 33, 25, and 66 MHz input clocks.

Table 63. Suggested PLL Configurations

Conf No.	SPMF	Core PLL	CEMF	CEDF	Input Clock Frequency (MHz)	CSB Frequency (MHz)	Core Frequency (MHz)	QUICC Engine Frequency (MHz)
1	0100	0000100	0110	0	33.33	133.33	266.66	200
2	0100	0000101	1000	0	25	100	250	200
3	0010	0000100	0011	0	66.67	133.33	266.66	200
4	0100	0000101	0110	0	33.33	133.33	333.33	200
5	0101	0000101	1000	0	25	125	312.5	200
6	0010	0000101	0011	0	66.67	133.33	333.33	200

23 Thermal

This section describes the thermal specifications of the MPC8323E.

23.1 Thermal Characteristics

Table 64 provides the package thermal characteristics for the 516 27 × 27 mm PBGA of the MPC8323E.

Table 64. Package Thermal Characteristics for PBGA

Characteristic	Board type	Symbol	Value	Unit	Notes
Junction-to-ambient natural convection	Single-layer board (1s)	R _{θJA}	28	°C/W	1, 2
Junction-to-ambient natural convection	Four-layer board (2s2p)	R _{θJA}	21	°C/W	1, 2, 3
Junction-to-ambient (@200 ft/min)	Single-layer board (1s)	R _{θJMA}	23	°C/W	1, 3
Junction-to-ambient (@200 ft/min)	Four-layer board (2s2p)	R _{θJMA}	18	°C/W	1, 3
Junction-to-board	—	R _{θJB}	13	°C/W	4
Junction-to-case	—	R _{θJC}	9	°C/W	5

interface. From this case temperature, the junction temperature is determined from the junction-to-case thermal resistance.

$$T_J = T_C + (R_{\theta JC} \times P_D)$$

where:

T_C = case temperature of the package (°C)

$R_{\theta JC}$ = junction-to-case thermal resistance (°C/W)

P_D = power dissipation (W)

24 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8323E.

24.1 System Clocking

The MPC8323E includes three PLLs.

- The system PLL (AV_{DD2}) generates the system clock from the externally supplied CLKIN input. The frequency ratio between the system and CLKIN is selected using the system PLL ratio configuration bits as described in [Section 22.4, “System PLL Configuration.”](#)
- The e300 core PLL (AV_{DD3}) generates the core clock as a slave to the system clock. The frequency ratio between the e300 core clock and the system clock is selected using the e300 PLL ratio configuration bits as described in [Section 22.5, “Core PLL Configuration.”](#)
- The QUICC Engine PLL (AV_{DD1}) which uses the same reference as the system PLL. The QUICC Engine block generates or uses external sources for all required serial interface clocks.

24.2 PLL Power Supply Filtering

Each of the PLLs listed above is provided with power through independent power supply pins. The voltage level at each AV_{DDn} pin should always be equivalent to V_{DD}, and preferably these voltages are derived directly from V_{DD} through a low frequency filter scheme such as the following.

There are a number of ways to reliably provide power to the PLLs, but the recommended solution is to provide five independent filter circuits as illustrated in [Figure 44](#), one to each of the five AV_{DD} pins. By providing independent filters to each PLL the opportunity to cause noise injection from one PLL to the other is reduced.

This circuit is intended to filter noise in the PLLs resonant frequency range from a 500 kHz to 10 MHz range. It should be built with surface mount capacitors with minimum effective series inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

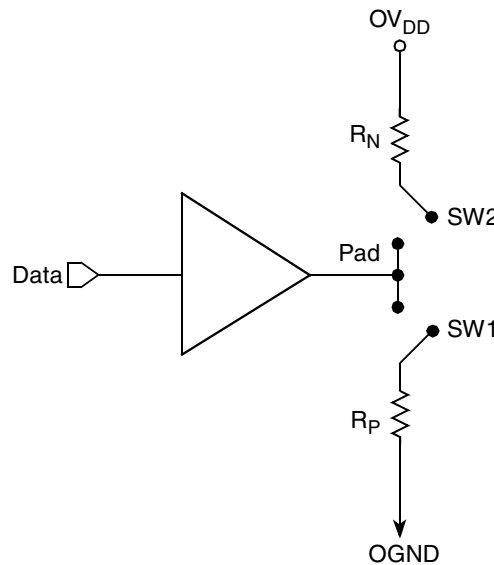


Figure 45. Driver Impedance Measurement

The value of this resistance and the strength of the driver's current source can be found by making two measurements. First, the output voltage is measured while driving logic 1 without an external differential termination resistor. The measured voltage is $V_1 = R_{source} \times I_{source}$. Second, the output voltage is measured while driving logic 1 with an external precision differential termination resistor of value R_{term} . The measured voltage is $V_2 = (1/(1/R_1 + 1/R_2)) \times I_{source}$. Solving for the output impedance gives $R_{source} = R_{term} \times (V_1/V_2 - 1)$. The drive current is then $I_{source} = V_1/R_{source}$.

Table 65 summarizes the signal impedance targets. The driver impedance are targeted at minimum V_{DD} , nominal OV_{DD} , 105°C.

Table 65. Impedance Characteristics

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	PCI	DDR DRAM	Symbol	Unit
R_N	42 Target	25 Target	20 Target	Z_0	W
R_P	42 Target	25 Target	20 Target	Z_0	W
Differential	NA	NA	NA	Z_{DIFF}	W

Note: Nominal supply voltages. See Table 1, $T_j = 105^\circ\text{C}$.

24.6 Configuration Pin Multiplexing

The MPC8323E provides the user with power-on configuration options which can be set through the use of external pull-up or pull-down resistors of 4.7 k Ω on certain output pins (see customer visible configuration pins). These pins are generally used as output only pins in normal operation.